Amendments to the Specification:

Please replace the paragraph beginning at page 9, line 6, with the following amended paragraph:

Fig. 3 shows the results of the dielectric breakdown test of the silicon oxide films of 1000 Å thick that had been formed on high-resistance silicon wafers using the present apparatus. Over the silicon oxide film, formed was a 1 mmø-aluminum electrode and the relation between the voltage and the current was plotted. ~~Fig. 3(C)~~ Curve (C) of Fig. 3 indicates the film that had been formed on the substrate without any particular treatment of the substrate prior to the filming, from which it is noted that the breakdown voltage of the film is low. The films of ~~Fig. 3(A)~~ curve (A) of Fig. 3 were formed as follows: After the substrates were set in the chamber, they were heated at 300°C and exposed to the plasma atmosphere generated by introducing 400 SCCM of oxygen and from 0 to 5 SCCM of TCE. The total pressure of the atmosphere was 5 Pa, and the RF power was 150 W. The plasma exposure was carried out for 10 minutes. (During the step, no film was formed by the gaseous reaction.) After the plasma exposure, the silicon oxide films of ~~Fig. 3(A)~~ curve (A) of Fig. 3 were formed, and they showed a high breakdown voltage.

Please replace the paragraph bridging pages 9 and 10 with the following amended paragraph:

The films of ~~Fig. 3(B)~~ curve (B) of Fig. 3 were formed as follows in the same manner as in ~~Fig. 3(A)~~ curve (A) of Fig. 3 except that the flow rate of TCE in the filming step was changed to 4 SCCM or more, for example 5 SCCM. As shown, they had a low breakdown voltage. From these results, it has been found that the TCE concentration for the filming has the optimum value.